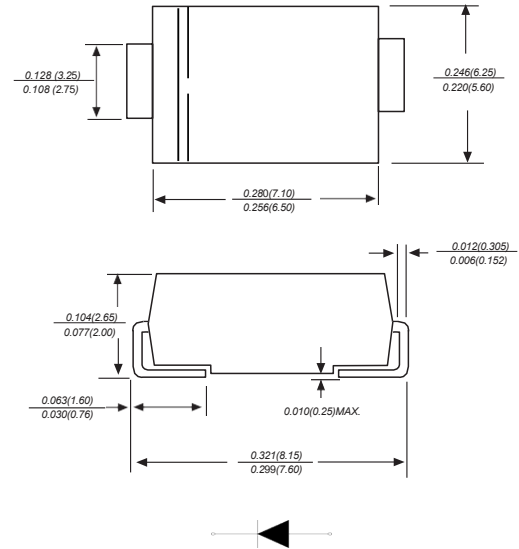


LOW FORWARD VOLTAGE SCHOTTKY BARRIER DIODES

Features

- ◆ The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- ◆ For surface mounted applications
- ◆ Metal silicon junction, majority carrier conduction
- ◆ Low power loss, high efficiency
- ◆ Built-in strain relief, ideal for automated placement
- ◆ High forward surge current capability
- ◆ High temperature soldering guaranteed:
260°C/10 seconds at terminals

DO-214AB/SMC



Dimensions in inches and (millimeters)

Maximum Ratings And Electrical Characteristics

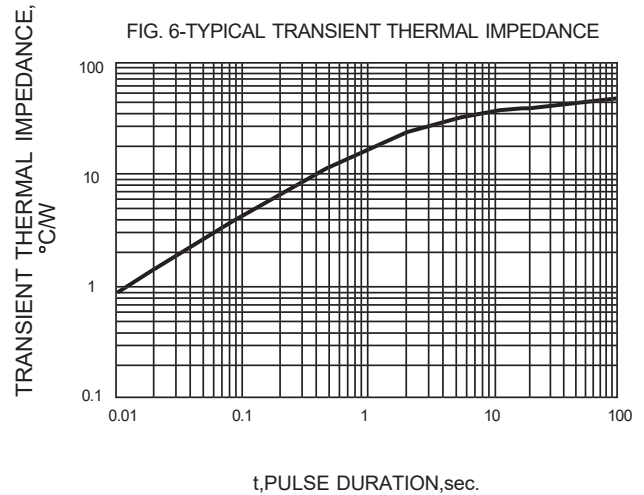
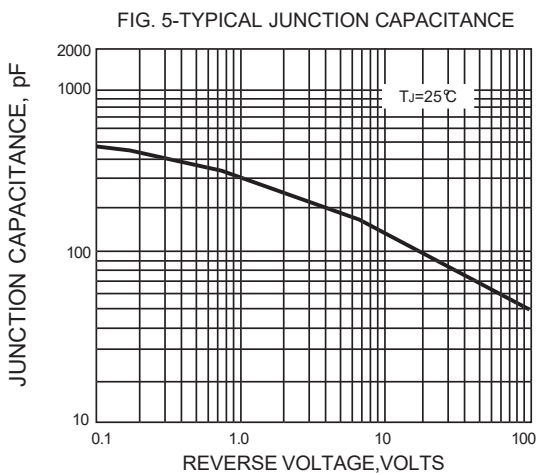
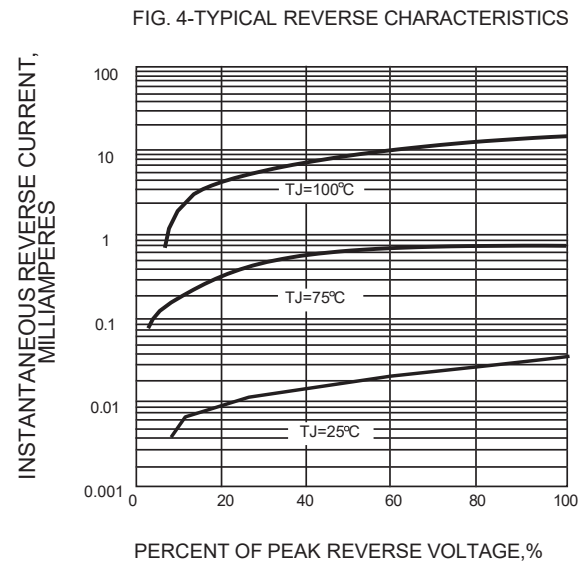
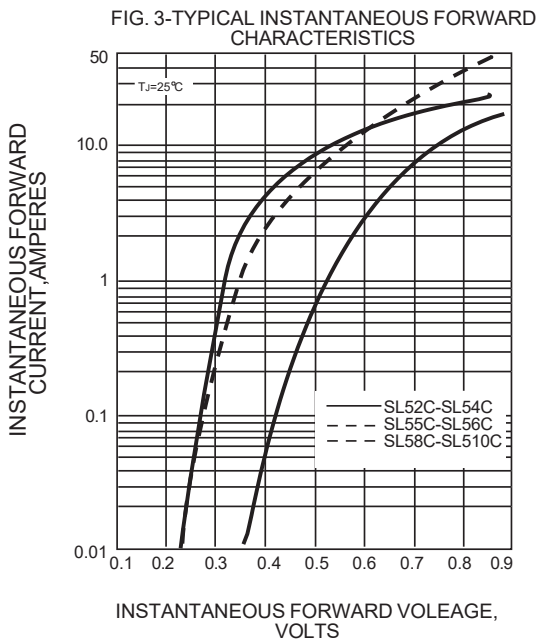
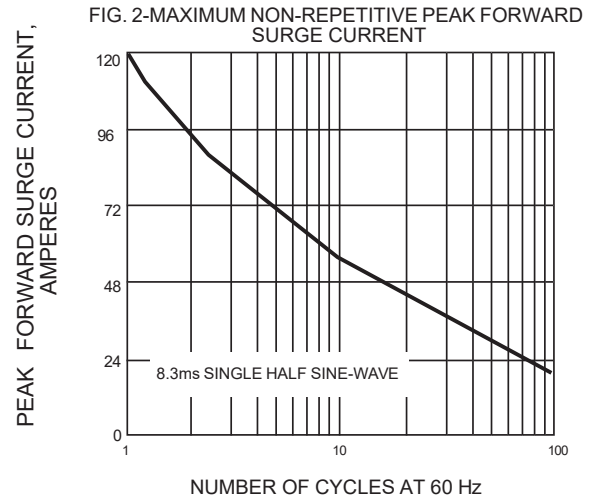
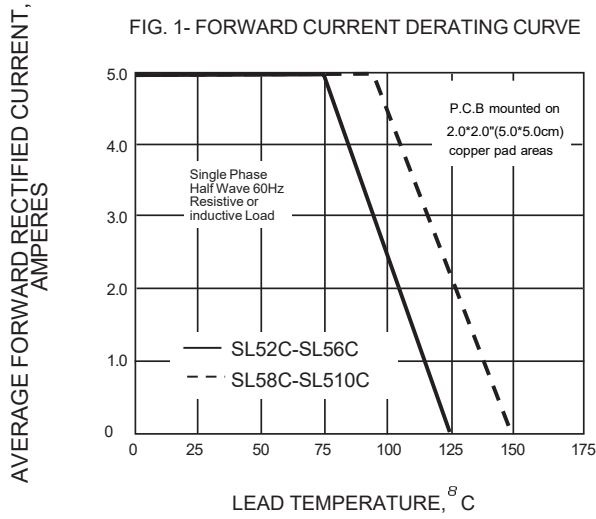
Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	SYMBOLS	SL52C	SL53C	SL54C	SL55C	SL56C	SL58C	SL510C	UNITS
Marking Code									
Maximum repetitive peak reverse voltage	V _{RRM}	20	30	40	50	60	80	100	V
Maximum RMS voltage	V _{RMS}	14	21	28	35	42	56	70	V
Maximum DC blocking voltage	V _{DC}	20	30	40	50	60	80	100	V
Maximum average forward rectified current at TL=90°C	I _(AV)	5.0							A
Peak forward surge current 8.3ms single half sine-wave superimposed onrated load (JEDEC Method)	I _{FSM}	120							A
Maximum instantaneous forward voltage at 5.0A	V _F	0.45			0.50		0.70		V
Maximum DCreverse current TA=25°C at rated DCblocking voltage TA=125°C	I _R	0.5 20.0					0.2 10.0		mA
Typical junction capacitance (NOTE 2)	C _J	200							pF
Typical thermal resistance (NOTE 3)	RθJA	55.0							°C/W
Operating junction and storage temperaturerange	T _J ,T _{STG}	-55 to +150							°C

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
2. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

Ratings And Characteristic Curves



The curve above is for reference only.